











**AWR1243** SWRS188 – MAY 2017

# AWR1243 Single-Chip 77- and 79-GHz FMCW Transceiver

# 1 Device Overview

# 1.1 Features

- FMCW Transceiver
  - Integrated PLL, Transmitter, Receiver, Baseband, and A2D
  - 76- to 81-GHz Coverage With 4 GHz Available Bandwidth
  - Four Receive Channels
  - Three Transmit Channels (Two Can be Used Simultaneously)
  - Ultra-Accurate Chirp Engine Based on Fractional-N PLL
  - TX Power: 12 dBm
  - RX Noise Figure:
    - 15 dB (76 to 77 GHz)
    - 16 dB (77 to 81 GHz)
  - Phase Noise at 1 MHz:
    - 94 dBc/Hz (76 to 77 GHz)
    - 91 dBc/Hz (77 to 81 GHz)
- · Built-in Calibration and Self-Test
  - Built-in Firmware (ROM)
  - Self-calibrating System Across Frequency and Temperature
- Host Interface
  - Control Interface With External Processor Over SPI
  - Data Interface With External Processor Over MIPI D-PHY and CSI2 V1.1
  - Interrupts for Fault Reporting

- ASIL B Capable
- AECQ100 Qualified
- AWR1243 Advanced Features
  - Embedded Self-monitoring With No Host Processor Involvement
  - Complex Baseband Architecture
  - Option of Cascading Multiple Devices to Increase Channel Count
  - Embedded Interference Detection Capability
- Power Management
  - Built-in LDO Network for Enhanced PSRR
  - I/Os Support Dual Voltage 3.3 V/1.8 V
- Clock Source
  - 40.0-MHz Crystal With Internal Oscillator
  - Supports External Oscillator at 40 and 50 MHz
- Easy Hardware Design
  - 0.65-mm Pitch, 161-Pin 10.4 mm x 10.4 mm
     Flip Chip BGA Package for Easy Assembly and Low-Cost PCB Design
  - Small Solution Size
- Supports Automotive Temperature Operating Range

# 1.2 Applications

- · Automated Highway Driving
- Automatic Emergency Braking

Adaptive Cruise Control

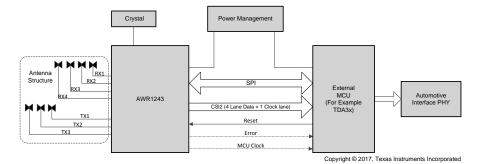


Figure 1-1. Radar Sensor for Automotive Applications



# 1.3 Description

The AWR1243 device is an integrated single-chip FMCW transceiver capable of operation in the 76- to 81-GHz band. The device enables unprecedented levels of integration in an extremely small form factor. AWR1243 is an ideal solution for low power, self-monitored, ultra-accurate radar systems in the automotive space.

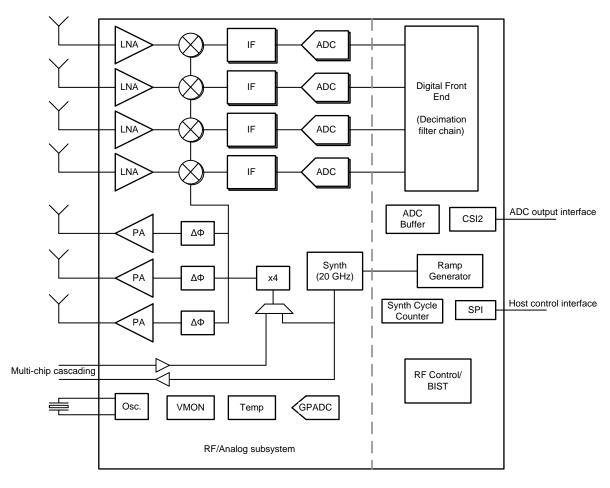
The AWR1243 device is a self-contained FMCW transceiver single-chip solution that simplifies the implementation of Automotive Radar sensors in the band of 76 to 81 GHz. It is built on Tl's low-power 45-nm RFCMOS process, which enables a monolithic implementation of a 3TX, 4RX system with built-in PLL and A2D converters. Simple programming model changes can enable a wide variety of sensor implementation (Short, Mid, Long) with the possibility of dynamic reconfiguration for implementing a multimode sensor. Additionally, the device is provided as a complete platform solution including reference hardware design, software drivers, sample configurations, API guide, and user documentation.

# Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE
X1243BIGABL (Tray)	FCBGA (161)	10.4 mm × 10.4 mm

(1) For more information, see Section 9, Mechanical Packaging and Orderable Information.

# 1.4 Functional Block Diagram





# **Table of Contents**

1	Devi	ice Overview <u>1</u>	6	Deta	ailed Description	27
	1.1	Features 1		6.1	Overview	27
	1.2	Applications 1		6.2	Functional Block Diagram	27
	1.3	Description		6.3	Subsystems	27
	1.4	Functional Block Diagram 2		6.4	Other Subsystems	30
2	Revi	ision History 3	7	App	lications, Implementation, and Layout	32
3	Devi	ice Comparison 4		7.1	Application Information	32
	3.1	Related Products 5		7.2	Short-, Medium-, and Long-Range Radar	32
4	Tern	ninal Configuration and Functions 6		7.3	Reference Schematic	32
	4.1	Pin Diagram 6		7.4	Layout	35
	4.2	Signal Descriptions	8	Devi	ice and Documentation Support	40
5	Spec	cifications 13		8.1	Device Nomenclature	40
	5.1	Absolute Maximum Ratings 13		8.2	Tools and Software	41
	5.2	ESD Ratings		8.3	Documentation Support	41
	5.3	Power-On Hours (POH)		8.4	Community Resources	42
	5.4	Recommended Operating Conditions		8.5	Trademarks	42
	5.5	Power Supply Specifications		8.6	Electrostatic Discharge Caution	42
	5.6	Power Consumption Summary 15		8.7	Export Control Notice	42
	5.7	RF Specification		8.8	Glossary	42
	5.8	Thermal Resistance Characteristics for FCBGA Package [ABL0161]	9		hanical, Packaging, and Orderable rmation	
	5.9	Timing and Switching Characteristics 18		9.1	Packaging Information	43

# 2 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
May 2017	*	Initial Release

# 3 Device Comparison

**Table 3-1. Device Features Comparison** 

FUNCTION		AWR1243	AWR1443	AWR1642
Number of receive	ers	4	4	4
Number of transmitters		3	3	2
On-chip memory		_	576KB	1.5MB
ASIL		B-Capable	_	B-Capable
Max interface (MH	lz)	15	5	5
Max real sampling	rate (Msps)	37.5	12.5	12.5
Processor		"	1	1
MCU (R4F)		_	Yes	Yes
DSP (C674x)		_	_	Yes
Peripherals				
Serial Peripheral I	nterface (SPI) ports	1	1	2
Quad Serial Peripl	heral Interface (QSPI)	_	Yes	Yes
Inter-Integrated Ci	rcuit (I <sup>2</sup> C) interface	_	1	1
Controller Area Ne	etwork (DCAN) interface	_	Yes	Yes
CAN FD		_	_	Yes
Trace		_	_	Yes
PWM		_	_	Yes
Hardware In Loop	(HIL/DMM)	_	_	Yes
GPADC		_	Yes	Yes
LVDS/Debug		Yes	Yes	Yes
CSI2		Yes	_	_
Hardware accelerator		_	Yes	_
1-V bypass mode		Yes	Yes	Yes
Cascade (20-GHz sync)		Yes	_	_
JTAG		_	Yes	Yes
Product status <sup>(1)</sup>	PRODUCT PREVIEW (PP), ADVANCE INFORMATION (AI), or PRODUCTION DATA (PD)	AI	AI	AI

<sup>(1)</sup> ADVANCE INFORMATION concerns new products in the sampling or preproduction phase of development. Characteristic data and other specifications are subject to change without notice.



# 3.1 Related Products

For information about other devices in this family of products or related products see the links that follow.

- mmWave Sensors TI's mmWave sensors rapidly and accurately sense range, angle and velocity with less power using the smallest footprint mmWave sensor portfolio for automotive applications.
- Automotive mmWave Sensors TI's automotive mmWave sensor portfolio offers high-performance radar front end to ultra-high resolution, small and low-power single-chip radar solutions. TI's scalable sensor portfolio enables design and development of ADAS system solution for every performance, application and sensor configuration ranging from comfort functions to safety functions in all vehicles.
- Companion Products for AWR1243 Review products that are frequently purchased or used in conjunction with this product.

# 4 Terminal Configuration and Functions

# 4.1 Pin Diagram

Figure 4-1 shows the pin locations for the 161-pin FCBGA package. Figure 4-2, Figure 4-3, Figure 4-4, and Figure 4-5 show the same pins, but split into four quadrants.

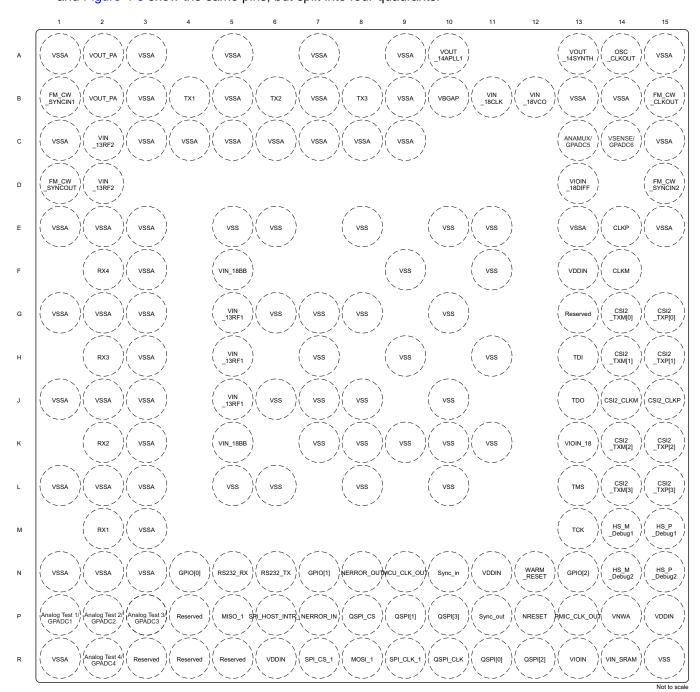


Figure 4-1. Pin Diagram

ADVANCE INFORMATION

**INSTRUMENTS** 

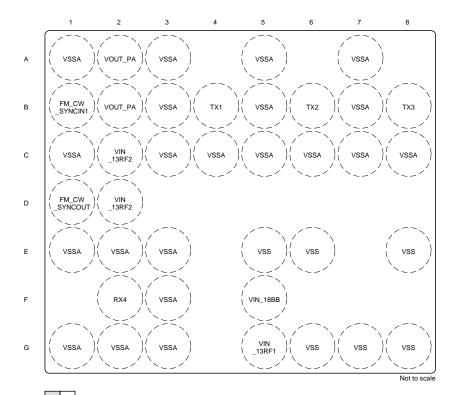


Figure 4-2. Top Left Quadrant

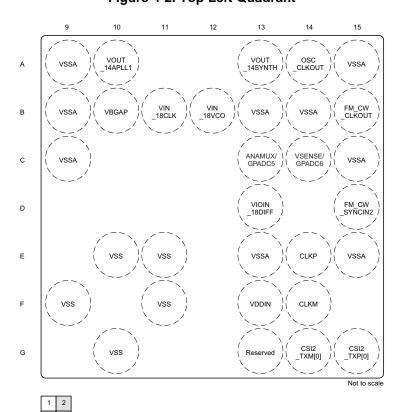


Figure 4-3. Top Right Quadrant

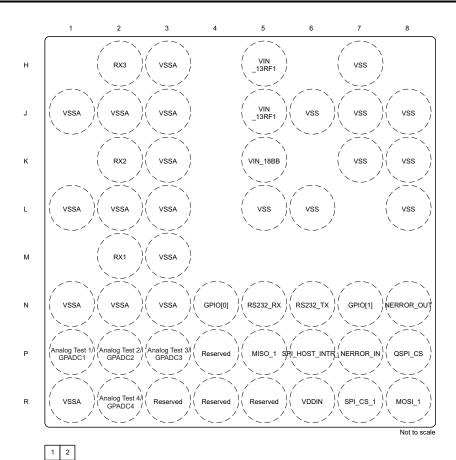


Figure 4-4. Bottom Left Quadrant

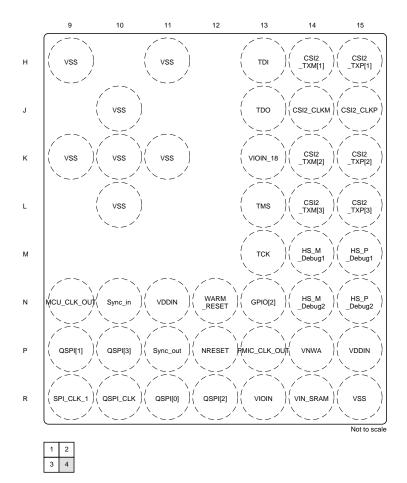


Figure 4-5. Bottom Right Quadrant

4.2

**Signal Descriptions** 

Table 4-1 lists the pins by function and describes that function.

**Table 4-1. Signal Descriptions** 

FUNCTION	SIGNAL NAME	PIN NUMBER	PIN	DESCRIPTION
FUNCTION	SIGNAL NAME	PIN NUMBER	TYPE	DESCRIPTION
	TX1	B4	0	Single-ended transmitter1 o/p
Transmitters	TX2	B6	0	Single-ended transmitter2 o/p
	TX3	B8	0	Single-ended transmitter3 o/p
	RX1	M2	I	Single-ended receiver1 i/p
Receivers	RX2	K2	I	Single-ended receiver2 i/p
Receivers	RX3	H2	- 1	Single-ended receiver3 i/p
	RX4	F2	- 1	Single-ended receiver4 i/p
	CSI2_TXP[0]	G15	0	Differential data Out – Lane 0
	CSI2_TXM[0]	G14	0	Differential data Out – Lane 0
	CSI2_CLKP	J15	0	Differential clock Out
	CSI2_CLKM	J14	0	Differential clock Out
	CSI2_TXP[1]	H15	0	Differential data Out   Long 1
	CSI2_TXM[1]	H14	0	− Differential data Out – Lane 1
0010 TV	CSI2_TXP[2]	K15	0	B.W 11-1-1-0-1-1-0-1
CSI2 TX	CSI2_TXM[2]	K14	0	Differential data Out – Lane 2
	CSI2_TXP[3]	L15	0	
	CSI2_TXM[3]	L14	0	Differential data Out – Lane 3
	HS_DEBUG1_P	M15	0	
	HS_DEBUG1_M	M14	0	Differential debug port 1
	HS_DEBUG2_P	N15	0	
	HS_DEBUG2_M	N14	0	Differential debug port 2
	FM_CW_CLKOUT	B15	0	20-GHz single-ended output. Modulated waveform
Chip-to-chip cascading	FM_CW_SYNCIN1	B1	I	20-GHz single-ended input. Only one of these pins should be
synchronization	FM_CW_SYNCIN2	D15	I	used. Multiple instances for layout flexibility.
signals	FM_CW_SYNCOUT	D1	0	20-GHz single-ended output for onboard loopback if desired
System	SYNC_OUT	P11	0	Low-frequency synchronization signal output
synchronization	SYNC_IN	N10	I	Low-frequency synchronization signal input
	SPI_CS_1	R7	I	SPI chip select
SPI control interface from	SPI_CLK_1	R9	I	SPI clock
external MCU	MOSI_1	R8	I	SPI data input
(default slave	MISO_1	P5	0	SPI data output
mode)	SPI_HOST_INTR_1	P6	0	SPI interrupt to host
	RESERVED	R3, R4, R5, P4		
	NRESET	P12	I	Power on reset for chip. Active low
Reset WARM_RESET N12		N12	Ю	Open-drain fail-safe warm reset signal. Can be driven from PMIC for diagnostic or can be used as status signal that the device is going through reset.
	NERROR_OUT	N8	0	Open-drain fail-safe output signal. Connected to PMIC/Processor/MCU to indicate that some severe criticality fault has happened. Recovery would be through reset.
Safety	NERROR_IN	P7	1	Fail-safe input to the device. Error output from any other device can be concentrated in the error signaling monitor module inside the device and appropriate action can be taken by firmware



**Table 4-1. Signal Descriptions (continued)** 

			-	
FUNCTION	SIGNAL NAME	PIN NUMBER	PIN TYPE	DESCRIPTION
	TMS	L13	I	
ITAC	TCK	M13	I	ITAC next fee steed dead become dead.
JTAG	TDI	H13	I	JTAG port for standard boundary scan
	TDO	J13	0	
Reference	CLKP	E14	I	OLKD is the Least and OLKM is the Output to this asserted
oscillator	CLKM	F14	0	CLKP is the Input and CLKM is the Output to drive crystal
Reference clock	OSC_CLKOUT	A14	0	Reference clock output from clocking subsystem after cleanup PLL. Can be used by slave chip in multichip cascading
Band-gap voltage	VBGAP	B10	0	
	VDDIN	F13,N11,P15, R6	POW	1.2-V digital power supply
	VIN_SRAM	R14	POW	1.2-V power rail for internal SRAM
	VNWA	P14	POW	1.2-V power rail for SRAM array back bias
	VIOIN	R13	POW	I/O supply (3.3-V or 1.8-V): All CMOS I/Os would operate on this supply.
	VIOIN_18	K13	POW	1.8-V supply for CMOS IO
	VIN_18CLK	B11	POW	1.8-V supply for clock module
	VIOIN_18DIFF	D13	POW	1.8-V supply for CSI2 port
	Reserved	G13	POW	No connect
	VIN_13RF1	G5,J5,H5	POW	1.3-V Analog and RF supply, VIN_13RF1 and VIN_13RF2
	VIN_13RF2	C2,D2	POW	could be shorted on the board
	VIN_18BB	K5,F5	POW	1.8-V Analog baseband power supply
	VIN_18VCO	B12	POW	1.8-V RF VCO supply
Power supply	vss	E5,E6,E8,E10, E11,F9,F11,G 6,G7,G8,G10, H7,H9,H11,J6, J7,J8,J10,K7,K 8,K9,K10,K11, L5,L6,L8,L10, R15	GND	Digital ground
9,A15,B3,I 7,B9,B13,I C1,C3,C4 C6,C7,C8 C15,E1,E2 E13,E15,F 1,G2,G3,H ,J2,J3,K3, 2,L3, M3,N1,N2		A1,A3,A5,A7,A 9,A15,B3,B5,B 7,B9,B13,B14, C1,C3,C4,C5, C6,C7,C8,C9, C15,E1,E2,E3, E13,E15,F3,G 1,G2,G3,H3,J1,J2,J3,K3,L1,L 2,L3, M3,N1,N2,N3, R1	GND	Analog ground
	VOUT_14APLL1	A10	0	
Internal LDO output/inputs	VOUT_14SYNTH	A13	0	
	VOUT_PA	A2,B2	0	
	PMIC_CLK_OUT	P13	0	Dithered clock input to PMIC
External clock out	MCU_CLK_OUT	N9	0	Programmable clock given out to external MCU or the processor
	GPIO[0]	N4	Ю	General-purpose IO
General-purpose I/Os	GPIO[1]	N7	Ю	General-purpose IO
	GPIO[2]	N13	Ю	General-purpose IO



# **Table 4-1. Signal Descriptions (continued)**

FUNCTION	SIGNAL NAME	PIN NUMBER	PIN TYPE	DESCRIPTION
	QSPI_CS	P8	0	Chip-select output from the device. Device is a master connected to serial flash slave.
QSPI for Serial	QSPI_CLK	R10	0	Clock output from the device. Device is a master connected to serial flash slave.
Flash (1)	QSPI[0]	R11	Ю	Data IN/OUT
	QSPI[1]	P9	Ю	Data IN/OUT
	QSPI[2]	R12	Ю	Data IN/OUT
	QSPI[3]	P10	Ю	Data IN/OUT
Flash programming	RS232_TX	N6	0	UART pins for programming external flash in
and RS232 UART <sup>(1)</sup>	RS232_RX	N5	ı	preproduction/debug hardware.
Test and Debug	Analog Test1 / GPADC1	P1	Ю	GP ADC channel 1
output for preproduction	Analog Test2 / GPADC2	P2	Ю	GP ADC channel 2
phase. Can be	Analog Test3 / GPADC3	P3	Ю	GP ADC channel 3
pinned out on	Analog Test4 / GPADC4	R2	Ю	GP ADC channel 4
production hardware for field	ANAMUX / GPADC5	C13	Ю	GP ADC channel 5
debug	VSENSE / GPADC6	C14	Ю	GP ADC channel 6

<sup>(1)</sup> This option is for development/debug in preproduction phase. Can be disabled by firmware pin mux setting.

# **ADVANCE INFORMATION**

# 5 Specifications

RUMENTS

# 5.1 Absolute Maximum Ratings(1)(2)

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
VDDIN	1.2 V digital power supply	-0.5	1.4	V
VIN_SRAM	1.2 V power rail for internal SRAM	-0.5	1.4	V
VNWA	1.2 V power rail for SRAM array back bias	-0.5	1.4	V
VIOIN	I/O supply (3.3 V or 1.8 V): All CMOS I/Os would operate on this supply.	-0.5	3.8	V
VIOIN_18	1.8 V supply for CMOS IO	-0.5	2	V
VIN_18CLK	1.8 V supply for clock module	-0.5	2	V
VIOIN_18DIFF	1.8 V supply for CSI2 port	-0.5	2	V
VIN_13RF1	1.3 V Analog and RF supply,VIN_13RF1 and VIN_13RF2 could be shorted on the board.	-0.5	1.45	V
VIN_13RF2		-0.5	1.45	V
VIN_13RF1 (1-V LDO bypass mode)	Device supports mode where external Power Management block can supply 1 V on VIN_13RF1 and VIN_13RF2 rails. In this configuration, the internal LDO of the device would be kept bypassed.	-0.5	1.4	V
VIN_13RF2 (1-V Internal LDO bypass mode)		-0.5	1.4	V
VIN_18BB	1.8-V Analog baseband power supply	-0.5	2	V
VIN_18VCO supply	1.8-V RF VCO supply	-0.5	2	V
In a district	Dual-voltage LVCMOS inputs, 3.3 V or 1.8 V (Steady State)	-0.3V	VIOIN + 0.3	
Input and output voltage range	Dual-voltage LVCMOS inputs, operated at 3.3 V/1.8 V (Transient Overshoot/Undershoot)		OIN + 20% up to of signal period	V
CLKP, CLKM	Input ports for reference crystal	-0.5	2	V
Clamp current	Input or Output Voltages 0.3 V above or below their respective power rails. Limit clamp current that flows through the internal diode protection cells of the I/O.	-20	20	mA
T <sub>J</sub>	Operating junction temperature range	-40	125	°C
T <sub>STG</sub>	Storage temperature range after soldered onto PC board	-55	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

# 5.2 ESD Ratings

			VALUE	UNIT
\/	Flootroototic discharge	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±1000	V
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per AEC Q100-011	±250	V

<sup>(1)</sup> AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

# 5.3 Power-On Hours (POH)<sup>(1)</sup>

OPERATING CONDITION	NOMINAL CVDD VOLTAGE (V)	JUNCTION TEMPERATURE (T <sub>j</sub> )	POWER-ON HOURS [POH] (HOURS)	
			–40°C	600 (6%)
1000/ duty ovala	1.2	75°C	2000 (20%)	
100% duty cycle	1.2	95°C	6500 (65%)	
		105°C	900 (9%)	

<sup>(1)</sup> This information is provided solely for your convenience and does not extend or modify the warranty provided under TI's standard terms and conditions for TI semiconductor products.

<sup>(2)</sup> All voltage values are with respect to V<sub>SS</sub>, unless otherwise noted.



# 5.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDDIN	1.2 V digital power supply	1.14	1.2	1.32	V
VIN_SRAM	1.2 V power rail for internal SRAM	1.14	1.2	1.32	V
VNWA	1.2 V power rail for SRAM array back bias	1.14	1.2	1.32	V
VIOIN	I/O supply (3.3 V or 1.8 V): All CMOS I/Os would operate on this supply.	3.15	3.3	3.45	V
VIOIN_18	1.8 V supply for CMOS IO	1.71	1.8	1.9	V
VIN_18CLK	1.8 V supply for clock module	1.71	1.8	1.9	V
VIOIN_18DIFF	1.8 V supply for CSI2 port	1.71	1.8	1.9	V
VIN_13RF1	1.3 V Analog and RF supply. VIN_13RF1 and VIN_13RF2 could be shorted on the board	1.23	1.3	1.36	V
VIN_13RF2		1.23	1.3	1.36	V
VIN_13RF1 (1-V Internal LDO bypass mode)	Device supports mode where external Power Management block can supply 1 V on VIN_13RF1 and VIN_13RF2 rails. In this configuration, the internal LDO of the device would be kept bypassed.	0.95	1	1.05	V
VIN_13RF2 (1-V Internal LDO bypass mode)	Device supports mode where external Power Management block can supply 1 V on VIN_13RF1 and VIN_13RF2 rails. In this configuration, the internal LDO of the device would be kept bypassed.	0.95	1	1.05	V
VIN18BB	1.8-V Analog baseband power supply	1.71	1.8	1.9	V
VIN_18VCO	1.8V RF VCO supply	1.71	1.8	1.9	V
.,	Voltage Input High (1.8 V mode)	1.17			V
$V_{IH}$	Voltage Input High (3.3 V mode)	2.25			V
\/	Voltage Input Low (1.8 V mode)			0.63	V
$V_{IL}$	Voltage Input Low (3.3 V mode)			0.8	V
V <sub>OH</sub>	High-level output threshold (I <sub>OH</sub> = 6 mA)	85%*VIOIN			mV
V <sub>OL</sub>	Low-level output threshold (I <sub>OL</sub> = 6 mA)			350	mV
CLKD CLKM	Voltage Input High	0.96			V
CLKP,CLKM	Voltage Input Low			0.24	V

# 5.5 Power Supply Specifications

Table 5-1 describes the four rails from an external power supply block of the AWR1243 device.

Table 5-1. Power Supply Rails Characteristics

SUPPLY	DEVICE BLOCKS POWERED FROM THE SUPPLY	RELEVANT IOS IN THE DEVICE
1.8 V	Synthesizer and APLL VCOs, crystal oscillator, IF Amplifier stages, ADC, CSI2	Input: VIN_18VCO, VIN18CLK, VIN_18BB, VIOIN_18DIFF, VIOIN_18IO LDO Output: VOUT_14SYNTH, VOUT_14APLL
1.3 V (or 1 V in internal LDO bypass mode)	Power Amplifier, Low Noise Amplifier, Mixers and LO Distribution	Input: VIN_13RF2, VIN_13RF1 LDO Output: VOUT_PA
3.3 V (or 1.8 V for 1.8 V I/O mode)	Digital I/Os	Input VIOIN
1.2 V	Core Digital and SRAMs	Input: VDDIN, VIN_SRAM

Table 5-2 lists tolerable ripple specifications for 1.3-V (1.0-V) and 1.8-V supply rails.

**Table 5-2. Ripple Specifications** 

	RF RAIL	VCO/IF RAIL	
FREQUENCY (kHz)	1.0 V (INTERNAL LDO BYPASS) (µV <sub>RMS</sub> )	1.3 V (μV <sub>RMS</sub> )	1.8 V (μV <sub>RMS</sub> )
137.5	7.76	648.73	83.41
275	5.83	76.48	21.27
550	3.44	22.74	11.43
1100	2.53	4.05	6.73
2200	11.29	82.44	13.39
4200	13.65	93.35	19.70
6600	22.91	117.78	29.63

# 5.6 Power Consumption Summary

Table 5-3 and Table 5-4 summarize the power consumption at the power terminals.

**Table 5-3. Maximum Current Ratings at Power Terminals** 

PARAMETER	SUPPLY NAME	DESCRIPTION	MIN	TYP	MAX	UNIT
	VDDIN, VIN_SRAM, VNWA	Total current drawn by all nodes driven by 1.2V rail			500	
Current consumption	VIN_13RF1, VIN_13RF2	Total current drawn by all nodes driven by 1.3V rail			2000	mA
Current consumption	VIOIN_18, VIN_18CLK, VIOIN_18DIFF, VIN_18BB, VIN_18VCO	Total current drawn by all nodes driven by 1.8V rail			850	IIIA
	VIOIN	Total current drawn by all nodes driven by 3.3V rail			50	

# **Table 5-4. Average Power Consumption at Power Terminals**

PARAMETER	CONDITION		DESCRIPTION	MIN	TYP	MAX	UNIT
Average power	1.0-V internal	1TX, 4RX	Campling: 16 66 MSps campley		1.73		
	LDO bypass mode	2TX, 4RX	Sampling: 16.66 MSps complex Transceiver, 40-ms frame time, 512 chirps, 512 samples/chirp, 8.5-µs interchirp time (50% duty cycle)		1.88		W
consumption	1.3-V internal	1TX, 4RX			1.92		VV
	LDO enabled mode	2TX, 4RX	Data Port: MIPI-CSI-2		2.1		



# 5.7 RF Specification

over recommended operating conditions (unless otherwise noted)

	PARAMETER		MIN	TYP	MAX	UNIT
	Naise Course	76 to 77 GHz		15		-ID
	Noise figure	77 to 81 GHz		16		dB
	1-dB compression point			<b>-</b> 5		dBm
	Maximum gain step			48		dB
	Gain range			24		dB
Receiver	Gain step size			2		dB
Receiver	IQ gain mismatch			1		dB
	IQ phase mismatch			2		degree
	IF bandwidth <sup>(1)</sup>			15	MHz	
	A2D sampling rate (real)			37.5	Msps	
	A2D sampling rate (complex)			18.75	Msps	
	A2D resolution			12		Bits
Transmitter	Output power		12		dBm	
rransmiller	Amplitude noise		-145		dBc/Hz	
	Frequency range		76		81	GHz
Clock	Ramp rate				100	MHz/µs
subsystem	Phase noise at 1-MHz offset	76 to 77 GHz		-94		dBc/Hz
	1 Hase Holse at 1-WH IZ OHSet	77 to 81 GHz		-91		UDC/11Z

(1) The analog IF stages include high-pass filtering, with two independently configurable first-order high-pass corner frequencies. The set of available HPF corners is summarized as follows:

Available HPF Corner Frequencies (kHz)

HPF1 HPF2

175, 235, 350, 700 350, 700, 1400, 2800

The filtering performed by the baseband chain is targeted to provide:

- Less than ±0.5 dB pass-band ripple/droop, and
- · Better than 60 dB anti-aliasing attenuation for any frequency that can alias back into the pass-band.

Figure 5-1 shows variations of noise figure and in-band P1dB parameters with respect to receiver gain programmed.

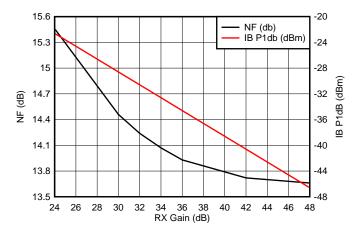


Figure 5-1. Noise Figure, In-band P1dB vs Receiver Gain

Table 5-5 describes the CSI-2 DPHY electrical specifications.



# Table 5-5. CSI-2 DPHY Electrical Specification

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	MIN	TYP	MAX	UNIT				
HSTX Driver	HSTX Driver								
V <sub>OD</sub>	HS transmit differential voltage <sup>(1)</sup>	140	200	270	mV				
V <sub>CMTX</sub>	HS transmit static common-mode voltage <sup>(1)</sup>	150	200	250	mV				
$ \Delta V_{OD} $	VOD mismatch when output is Differential-1 or Differential-0			10	mV				
$ \Delta V_{CMTX(1,0)} $	VCMTX mismatch when output is Differential-1 or Differential-0			5	mV				
V <sub>OHHS</sub>	HS output high voltage <sup>(1)</sup>			360	mV				
Z <sub>OS</sub>	Single-ended output impedance	40	50	62.5	Ω				
$\Delta Z_{OS}$	Single-ended output impedance mismatch			10%					
LPTX Driver									
$V_{OL}$	Thevenin output low level	-50		50	mV				
V <sub>OH</sub>	Thevenin output high level	1.1	1.2	1.3	V				
Z <sub>OLP</sub>	Output impedance of LP transmitter	110			Ω				

<sup>(1)</sup> Value when driving into differential load impedance anywhere in the range from 80 to 125  $\Omega$ .

# 5.8 Thermal Resistance Characteristics for FCBGA Package [ABL0161]<sup>(1)</sup>

THERMAL	THERMAL METRICS <sup>(2)</sup>	
$R\Theta_{JC}$	Junction-to-case	4.92
$R\Theta_{JB}$	Junction-to-board	6.57
$R\Theta_{JA}$	Junction-to-free air	22.3
$R\Theta_{JMA}$	Junction-to-moving air	N/A <sup>(1)</sup>
Psi <sub>JT</sub>	Junction-to-package top	4.92
Psi <sub>JB</sub>	Junction-to-board	6.4

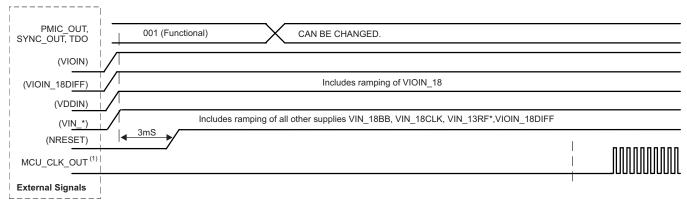
- (1) N/A = not applicable
- (2) For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.
- (3) °C/W = degrees Celsius per watt.
- (4) These values are based on a JEDEC-defined 2S2P system (with the exception of the Theta JC [RΘ<sub>JC</sub>] value, which is based on a JEDEC-defined 1S0P system) and will change based on environment as well as application. For more information, see these EIA/JEDEC standards:
  - JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions Natural Convection (Still Air)
  - JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages
  - JESD51-7, High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages
  - JESD51-9, Test Boards for Area Array Surface Mount Package Thermal Measurements

A junction temperature of 125°C is assumed.

# 5.9 Timing and Switching Characteristics

# 5.9.1 Power Supply Sequencing and Reset Timing

The AWR1243 device expects all external voltage rails to be stable before reset is deasserted. Figure 5-2 describes the device wake-up sequence.



(1) MCU\_CLK\_OUT in autonomous mode, where AWR1243 application is booted from the serial flash, MCU\_CLK\_OUT is not enabled by default by the device bootloader.

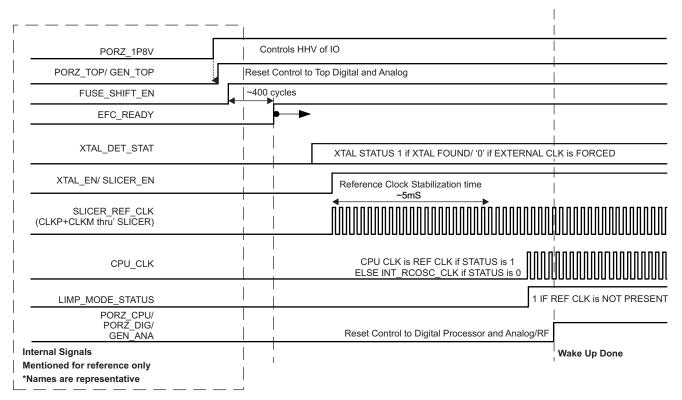


Figure 5-2. Device Wake-up Sequence



# 5.9.2 Input Clocks and Oscillators

# 5.9.2.1 Clock Specifications

An external crystal is connected to the device pins. Figure 5-3 shows the crystal implementation.

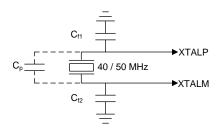


Figure 5-3. Crystal Implementation

## NOTE

The load capacitors,  $C_{f1}$  and  $C_{f2}$  in Figure 5-3, should be chosen such that Equation 1 is satisfied.  $C_L$  in the equation is the load specified by the crystal manufacturer. All discrete components used to implement the oscillator circuit should be placed as close as possible to the associated oscillator CLKP and CLKM pins.

$$C_{L} = C_{f1} \times \frac{C_{f2}}{C_{f1} + C_{f2}} + C_{P}$$
(1)

Table 5-6 lists the electrical characteristics of the clock crystal.

**Table 5-6. Crystal Electrical Characteristics** 

NAME	DESCRIPTION	MIN	TYP	MAX	UNIT
f <sub>P</sub>	Parallel resonance crystal frequency		40, 50		MHz
C <sub>L</sub>	Crystal load capacitance	5	8	12	pF
ESR	Crystal ESR			50	Ω
Temperature range	Expected temperature range of operation	-40		150	°C
Frequency tolerance	Crystal frequency tolerance (1)(2)	-50		50	ppm
Drive level			50	200	μW

<sup>(1)</sup> The crystal manufacturer's specification must satisfy this requirement.

<sup>(2)</sup> Includes initial tolerance of the crystal, drift over temperature, aging and frequency pulling due to incorrect load capacitance.



# 5.9.3 Multibuffered / Standard Serial Peripheral Interface (MibSPI)

# 5.9.3.1 Peripheral Description

The MibSPI/SPI is a high-speed synchronous serial input/output port that allows a serial bit stream to be shifted into and out of the device at a programmed bit-transfer rate. The MibSPI/SPI is normally used for communication between the microcontroller and external peripherals or another microcontroller.

Table 5-8 and Table 5-9 assume the operating conditions stated in Table 5-7. Table 5-8, Table 5-9, and Figure 5-4 describe the timing and switching characteristics of the MibSPI transmit and receive RAM organization.

**Table 5-7. SPI Timing Conditions** 

		MIN	TYP MAX	UNIT		
Input Cond	litions					
$t_R$	Input rise time	1	3	ns		
t <sub>F</sub>	Input fall time	1	3	ns		
Output Co	Output Conditions					
$C_{LOAD}$	Output load capacitance	2	15	pF		

Table 5-8. SPI Slave Mode Switching Parameters (SPICLK = input, SPISIMO = input, and SPISOMI = output)<sup>(1)</sup>

NO.		PARAMETER		TYP M	AX	UNIT
1	t <sub>c(SPC)S</sub>	Cycle time, SPICLK	25			ns
2	t <sub>w(SPCH)S</sub>	Pulse duration, SPICLK high (clock polarity = 0)	10			ns
3	t <sub>w(SPCL)S</sub>	Pulse duration, SPICLK low (clock polarity = 0)	10			ns
4	t <sub>d(SPCH-SOMI)</sub> S	Delay time, SPISOMI valid after SPICLK high (clock polarity = 0)			10	ns
5	t <sub>h(SPCH-SOMI)S</sub>	Hold time, SPISOMI data valid after SPICLK high (clock polarity = 0)	2			ns

<sup>(1)</sup> The mode of operation is mode 0 (clock polarity = 0; clock phase = 0).

Table 5-9. SPI Slave Mode Timing Requirements (SPICLK = input, SPISIMO = input, and SPISOMI = output)

NO.		MIN	TYP	MAX	UNIT
1	$t_{SU(SIMO-SPCL)S}$ Setup time, SPISIMO before SPICLK low (clock polarity = 0)	3			ns
2	t <sub>h(SPCL-SIMO)S</sub> Hold time, SPISIMO data valid after SPICLK low (clock polarity = 0)	0			ns

**STRUMENTS** 

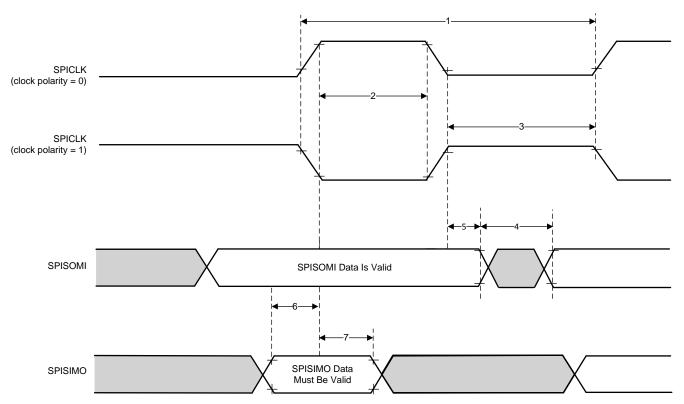


Figure 5-4. SPI Slave Mode External Timing

# Typical Interface Protocol Diagram (Slave Mode)

1. Host should ensure that there is a delay of two SPI clocks between CS going low and start of SPI clock.

2. Host should ensure that CS is toggled for every 16 bits of transfer through SPI.

Figure 5-5 shows the SPI communication timing of the typical interface protocol.

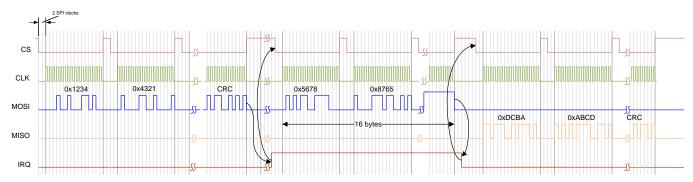


Figure 5-5. SPI Communication



# 5.9.4 General-Purpose Input/Output

Table 5-10 lists the switching characteristics of output timing relative to load capacitance.

Table 5-10. Switching Characteristics for Output Timing versus Load Capacitance  $(C_L)^{(1)(2)}$ 

PARAMETER		TEST CO	ONDITIONS	VIOIN = 1.8V	VIOIN = 3.3V	UNIT
			C <sub>L</sub> = 20 pF	2.878	3.013	
t <sub>r</sub>	Max rise time		$C_L = 50 pF$	6.446	6.947	ns
		Slew control = 0	$C_L = 75 pF$	9.43	10.249	
		-	$C_L = 20 pF$	2.827	2.883	
t <sub>f</sub>	Max fall time		$C_L = 50 pF$	6.442	6.687	ns
			C <sub>L</sub> = 75 pF	9.439	9.873	
			C <sub>L</sub> = 20 pF	3.307	3.389	
t <sub>r</sub>	Max rise time		$C_L = 50 pF$	6.77	7.277	ns
		Class control 1	$C_L = 75 pF$	9.695	10.57	
		Slew control = 1	$C_L = 20 pF$	3.128	3.128	
t <sub>f</sub>	Max fall time		$C_L = 50 pF$	6.656	6.656	ns
			C <sub>L</sub> = 75 pF	9.605	9.605	

<sup>(1)</sup> Slew control, which is configured by PADxx\_CFG\_REG, changes behavior of the output driver (faster or slower output slew rate).

<sup>(2)</sup> The rise/fall time is measured as the time taken by the signal to transition from 10% and 90% of VIOIN voltage.

# 5.9.5 Camera Serial Interface (CSI)

The CSI is a MIPI D-PHY compliant interface for connecting this device to a camera receiver module. This interface is made of four differential lanes; each lane is configurable for carrying data or clock. The polarity of each wire of a lane is also configurable. Table 5-11, Figure 5-6, Figure 5-7, and Figure 5-8 describe the clock and data timing of the CSI.

# Table 5-11. CSI Switching Characteristics

over operating free-	air temperature range (unless otherw	ise noted)				
	PARAMETER		MIN	TYP	MAX	UNIT
HPTX						
⊔ <b>ст</b> ∨	Data bit rate	(1 or 2 data lane PHY)	150		900	Mhne
HSTX <sub>DBR</sub>	Data bit fate	(4 data lane PHY)	150		600	Mbps
4	DDD alsolv fragues as	(1 or 2 data lane PHY)	75		450	NAL I-
fclk	DDR clock frequency	(4 data lane PHY)	75		300	MHz
$\Delta_{\text{VCMTX(LF)}}$	Common-level variation from 75 t frequency	o 450 MHz of CSI2 clock	-50		50	mVpeak
t <sub>R</sub> and t <sub>F</sub>	20% to 80% rise time and fall time	Δ .	150			ns
iR and if	2070 to 0070 fise time and fair time	20 /			0.3	UI
LPTX DRIVER						
t <sub>RLP</sub> and t <sub>FLP</sub>	15% to 85% rise time and fall time	е			25	ns
t <sub>EOT</sub> <sup>(1)</sup>	Time from start of THS-TRAIL per	riod to start of LP-11 state			105 + 12*UI	ns
δV/δt <sub>SR</sub> <sup>(2)(3)(4)</sup>	Slew rate. C <sub>LOAD</sub> = 0 to 5 pF				500	
	Slew rate. $C_{LOAD} = 5$ to 20 pF	Slew rate. C <sub>LOAD</sub> = 5 to 20 pF			200	mV/ns
	Slew rate. $C_{LOAD} = 20$ to 70 pF	Slew rate. C <sub>LOAD</sub> = 20 to 70 pF			100	
C <sub>LOAD</sub> <sup>(2)</sup>	Load capacitance	0		70	pF	
DATA-CLOCK Timing	Specification					
LUNOM	Nominal unit interval (1, 2, or 3 data lane PHY)		1.11		13.33	no
UINOM	Nominal unit interval (4 data lane	1.67		13.33	ns	
UIINST,MIN	Minimum instantaneous Unit Inter	rval (1, 2, or 3 data lane PHY)	1.033	0.975*U INOM – 0.05		ns
	Minimum instantaneous Unit Inter	Minimum instantaneous Unit Interval (4 data lane PHY)				
TSKEW[TX]	Data to clock skew measured at t	ransmitter	-0.15		0.15	UIINST, MIN
CSI2 TIMING SPECIF	FICATION					
T <sub>CLK-MISS</sub>	Time-out for receiver to detect ab disable the clock lane HS-RX.	sence of clock transitions and			60	ns
T <sub>CLK-POST</sub>	last associated data lane has tran	Time that the transmitter continues to send HS clock after the last associated data lane has transitioned to Ip mode. Interval is defined as the period from the end of T <sub>HS-TRAIL</sub> to the beginning				ns
T <sub>CLK-PRE</sub>		Time that the HS clock shall be driven by the transmitter before any associated data lane beginning the transition from LP to HS mode.				ns
T <sub>CLK-PREPARE</sub>		Time that the transmitter drives the clock lane LP-00 line state immediately before the HS-0 line state starting the HS transmission.			95	ns
T <sub>CLK-SETTLE</sub>	Time interval during which the HS clock lane HS transitions, starting PREPARE.		95		300	ns

- (1) With an additional load capacitance CCM of 0 to 60 pF on the termination center tap at RX side of the lane
- (2) While driving C<sub>LOAD</sub>. Load capacitance includes 50 pF of transmission line capacitance, and 10 pF each for TX and RX.
- When the output voltage is from 15% to 85% of the fully settled LP signal levels
- (4) Measured as average across any 50 mV segment of the output signal transition



# Table 5-11. CSI Switching Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP MAX	UNIT
T <sub>CLK-TERM-EN</sub>	Time for the clock lane receiver to enable the HS line termination, starting from the time point when Dn crosses VIL,MAX.	Time for Dn to reach VTERM-EN	38	3 ns
T <sub>CLK-TRAIL</sub>	Time that the transmitter drives the HS-0 state after the last payload clock bit of a HS transmission burst.	60		ns
T <sub>CLK-PREPARE</sub> + T <sub>CLK-ZERO</sub>	T <sub>CLK-PREPARE</sub> + time that the transmitter drives the HS-0 state before starting the clock.	300		ns
T <sub>D-TERM-EN</sub>	Time for the data lane receiver to enable the HS line termination, starting from the time point when Dn crosses VIL,MAX.	Time for Dn to reach VTERM-EN	35 ns - 4*U	ne
T <sub>EOT</sub>	Transmitted time interval from the start of $T_{\text{HS-TRAIL}}$ or $T_{\text{CLKTRAIL}}$ , to the start of the LP-11 state following a HS burst.		105 ns - n*12*U	- ns
T <sub>HS-PREPARE</sub>	Time that the transmitter drives the data lane LP-00 line state immediately before the HS-0 line state starting the HS transmission	40 + 4*UI	85 - 6*U	
T <sub>HS-PREPARE</sub> + T <sub>HS-ZERO</sub>	T <sub>HS-PREPARE</sub> + time that the transmitter drives the HS-0 state prior to transmitting the Sync sequence.	145 ns + 10*UI		ns
T <sub>HS-SETTLE</sub>	Time interval during which the HS receiver shall ignore any data lane HS transitions, starting from the beginning of T <sub>HSPREPARE</sub> . The HS receiver shall ignore any data lane transitions before the minimum value, and he HS receiver shall respond to any data lane transitions after the maximum value.	85 ns + 6*UI	145 n: + 10*U	ne
T <sub>HS-SKIP</sub>	Time interval during which the HS-RX should ignore any transitions on the data lane, following a HS burst. The end point of the interval is defined as the beginning of the LP-11 state following the HS burst.	40	55 ns - 4*U	ne
T <sub>HS-EXIT</sub>	Time that the transmitter drives LP-11 following a HS burst.	100		ns
T <sub>HS-TRAIL</sub>	Time that the transmitter drives the flipped differential state after last payload data bit of a HS transmission burst	max(n*8*UI, 60 ns + n*4*UI) <sup>(5)(6)</sup>		ns
T <sub>LPX</sub>	Transmitted length of any low-power state period	50 <sup>(7)</sup>	· · · · · · · · · · · · · · · · · · ·	ns

- If a > b then max(a, b) = a, otherwise max(a, b) = b.
- (6) Where n = 1 for Forward-direction HS mode and n = 4 for Reverse-direction HS mode
- T<sub>LPX</sub> is an internal state machine timing reference. Externally measured values may differ slightly from the specified values due to asymmetrical rise and fall times.

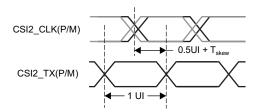


Figure 5-6. Clock and Data Timing in HS Transmission

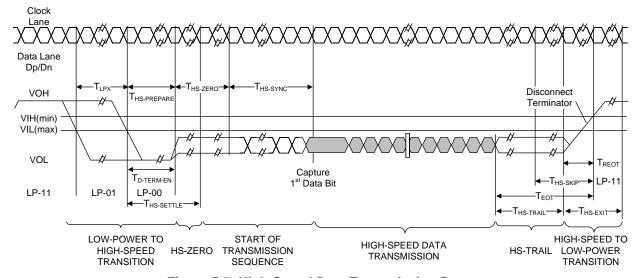


Figure 5-7. High-Speed Data Transmission Burst

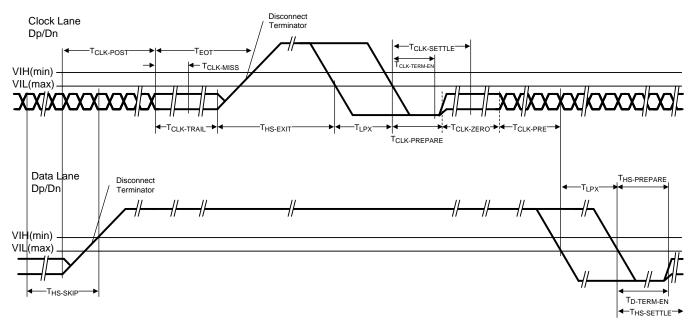


Figure 5-8. Switching the Clock Lane Between Clock Transmission and Low-Power Mode

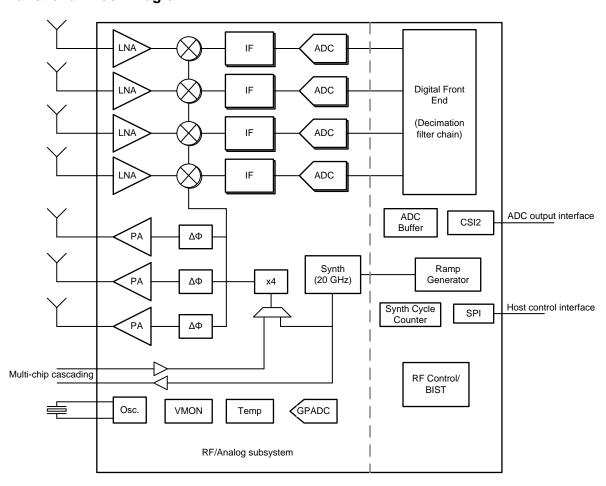


# **Detailed Description**

### Overview 6.1

The AWR1243 device is a single-chip highly integrated 77-GHz transceiver and front end that includes three transmit and four receive chains. The device can be used in long-range automotive radar applications such as automatic emergency braking and automatic adaptive cruise control. The AWR1243 has extremely small form factor and provides ultra-high resolution with very low power consumption. This device, when used with the TDA3X or TD2X, offers higher levels of performance and flexibility through a programmable digital signal processor (DSP); thus addressing the standard short-, mid-, and long-range automotive radar applications.

### 6.2 **Functional Block Diagram**



### 6.3 **Subsystems**

# 6.3.1 RF and Analog Subsystem

The RF and analog subsystem includes the RF and analog circuitry – namely, the synthesizer, PA, LNA, mixer, IF, and ADC. This subsystem also includes the crystal oscillator and temperature sensors. The three transmit channels can be operated up to a maximum of two at a time (simultaneously) for transmit beamforming purpose as required; whereas the four receive channels can all be operated simultaneously.



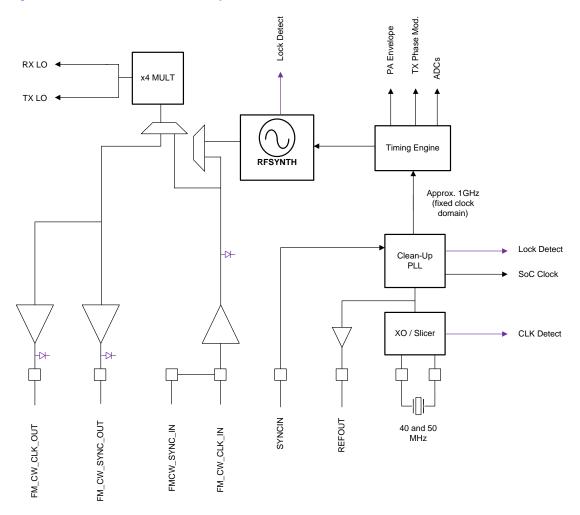
# 6.3.1.1 Clock Subsystem

The AWR1243 clock subsystem generates 76 to 81 GHz from an input reference of 40-MHz crystal. It has a built-in oscillator circuit followed by a clean-up PLL and a RF synthesizer circuit. The output of the RF synthesizer is then processed by an X4 multiplier to create the required frequency in the 76- to 81-GHz spectrum. The RF synthesizer output is modulated by the timing engine block to create the required waveforms for effective sensor operation.

The output of the RF synthesizer is available at the device pin boundary for multichip cascaded configuration. The clean-up PLL also provides a reference clock for the host processor after system wakeup.

The clock subsystem also has built-in mechanisms for detecting the presence of a crystal and monitoring the quality of the generated clock.

Figure 6-1 describes the clock subsystem.



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Figure 6-1. Clock Subsystem

# **ADVANCE INFORMATION**

# 6.3.1.2 Transmit Subsystem

STRUMENTS

The AWR1243 transmit subsystem consists of three parallel transmit chains, each with independent phase and amplitude control. A maximum of two transmit chains can be operational at the same time. However all three chains can be operated together in a time-multiplexed fashion. The device supports binary phase modulation for MIMO radar and interference mitigation.

Each transmit chain can deliver a maximum of 12 dBm at the antenna port on the PCB. The transmit chains also support programmable backoff for system optimization.

Figure 6-2 describes the transmit subsystem.

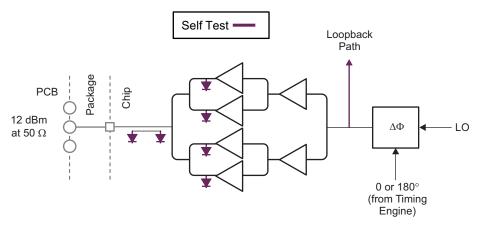


Figure 6-2. Transmit Subsystem (Per Channel)

# 6.3.1.3 Receive Subsystem

The AWR1243 receive subsystem consists of four parallel channels. A single receive channel consists of an LNA, mixer, IF filtering, A2D conversion, and decimation. All four receive channels can be operational at the same time an individual power-down option is also available for system optimization.

Unlike conventional real-only receivers, the AWR1243 device supports a complex baseband architecture, which uses quadrature mixer and dual IF and ADC chains to provide complex I and Q outputs for each receiver channel. The AWR1243 is targeted for fast chirp systems. The band-pass IF chain has configurable lower cutoff frequencies above 350 kHz and can support bandwidths up to 15 MHz.

Figure 6-3 describes the receive subsystem.

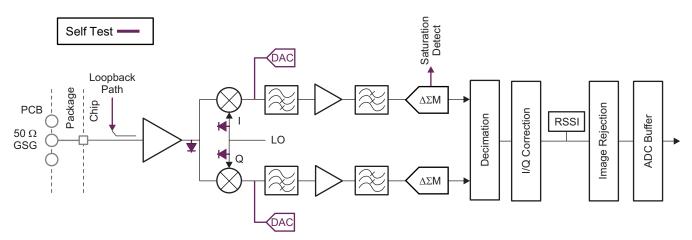


Figure 6-3. Receive Subsystem (Per Channel)

# 6.3.2 Host Interface

The AWR1243 device communicates with the host radar processor over the following main interfaces:

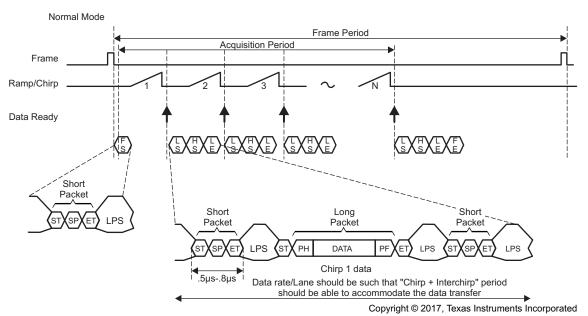
- Reference Clock Reference clock available for host processor after device wakeup
- Control 4-port standard SPI (slave) for host control. All radio control commands (and response) flow through this interface.
- Data High-speed serial port following the MIPI CSI2 format. Four data and one clock lane (all differential). Data from different receive channels can be multiplexed on a single data lane to optimize board routing. This is a unidirectional interface used for data transfer only.
- Reset Active-low reset for device wakeup from host
- Out-of-band interrupt
- Error Used for notifying the host in case the radio controller detects a fault

# 6.4 Other Subsystems

# 6.4.1 A2D Data Format Over CSI2 Interface

The AWR1243 device uses MIPI D-PHY / CSI2-based format to transfer the raw A2D samples to the external MCU. This is shown in Figure 6-4.

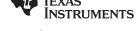
- Supports four data lanes
- CSI-2 data rate scalable from 150 Mbps to 900 Mbps per lane (If four lanes are used simultaneously then the maximum data rate supported is 600 Mbps per lane)
- · Virtual channel based
- CRC generation



Frame Start – CSi2 VSYNC Start Short Packet Line Start – CSI2 HSYNC Start Short Packet Line End – CSI2 HSYNC End Short Packet Frame End – CSi2 VSYNC End Short Packet

Figure 6-4. CSI-2 Transmission Format

ADVANCE INFORMATION



The data payload is constructed with the following three types of information:

- Chirp profile information
- The actual chirp number
- A2D data corresponding to chirps of all four channels
  - Interleaved fashion
- Chirp quality data (configurable)

The payload is then split across the four physical data lanes and transmitted to the receiving D-PHY. The data packet packing format is shown in Figure 6-5

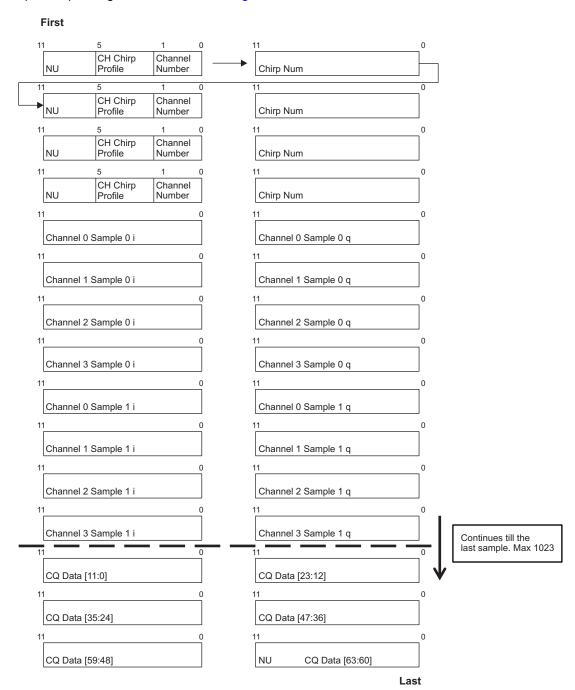


Figure 6-5. Data Packet Packing Format for 12-Bit Complex Configuration



# 7 Applications, Implementation, and Layout

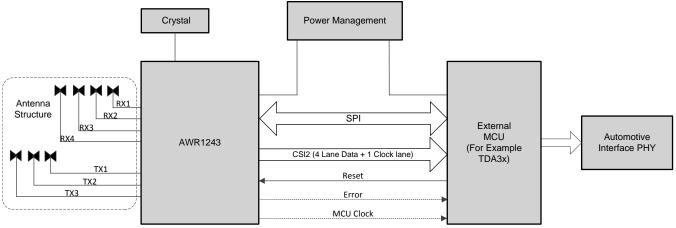
## **NOTE**

Information in the following Applications section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

# 7.1 Application Information

A typical application addresses the standard short-, mid-, long-range, and high-performance imaging radar applications with this radar front end and external programmable MCU. Figure 7-1 shows a short-, medium-, or long-range radar application.

# 7.2 Short-, Medium-, and Long-Range Radar



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Figure 7-1. Short-, Medium-, and Long-Range Radar

# 7.3 Reference Schematic

Figure 7-2 and Figure 7-3 show the reference schematic and low-noise LDO circuitry for the AWR1243 device.

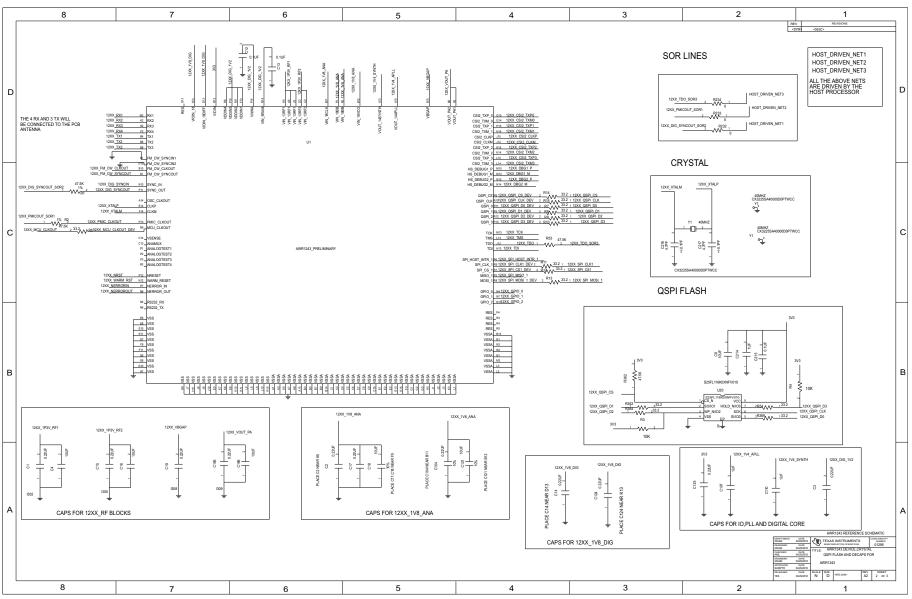


Figure 7-2. AWR1243 Reference Schematic

**ADVANCE INFORMATION** 



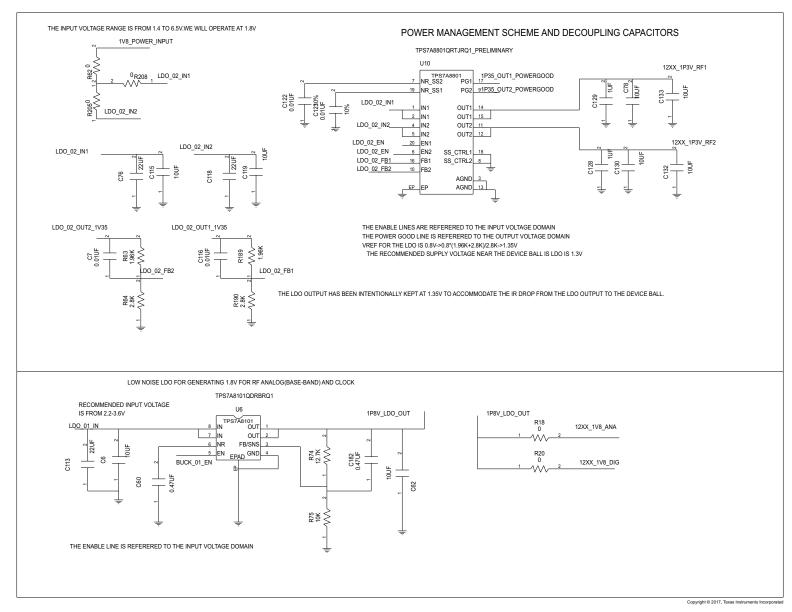


Figure 7-3. AWR1243 Low-Noise LDO Circuitry



### 7.4 Layout

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The top layer routing, top layer closeup, and bottom layer routing are shown in Figure 7-4, Figure 7-5, and Figure 7-6, respectively.

# 7.4.1 Layout Guidelines

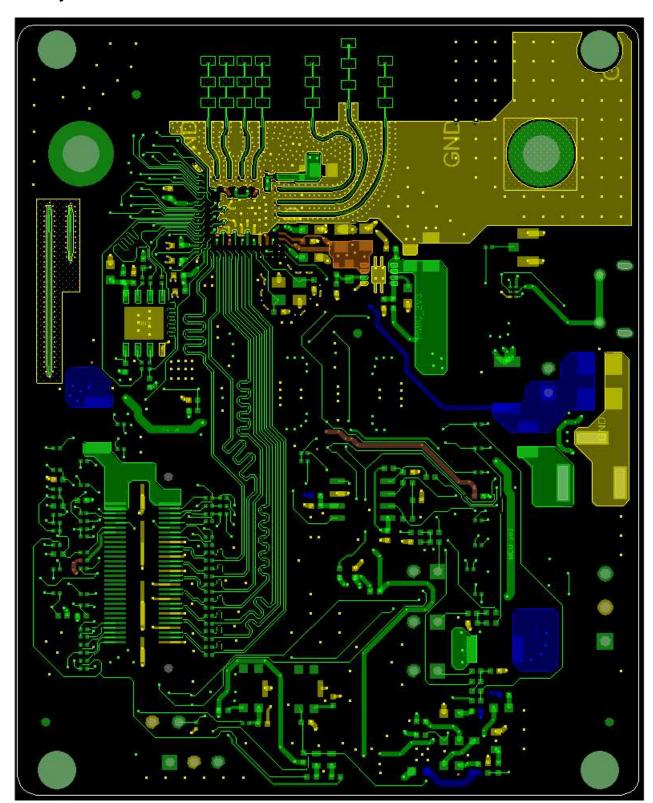


Figure 7-4. Top Layer Routing



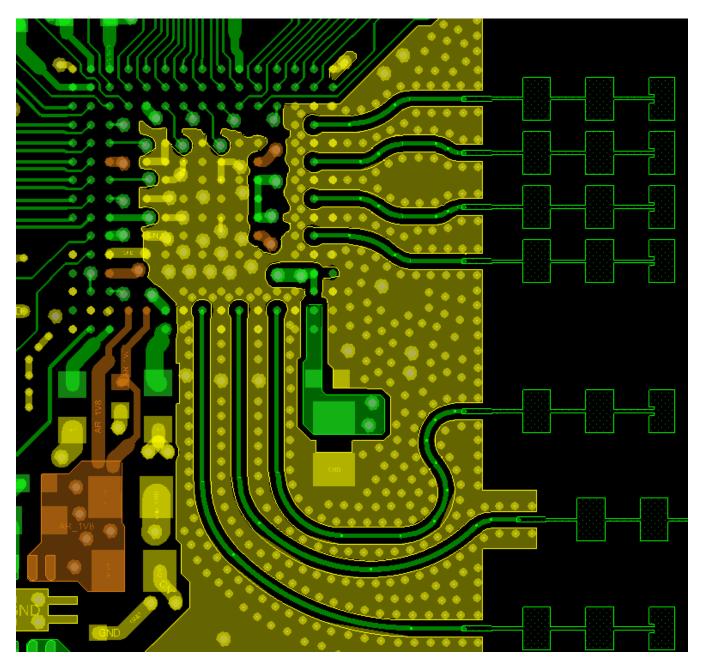


Figure 7-5. Top Layer Routing Closeup

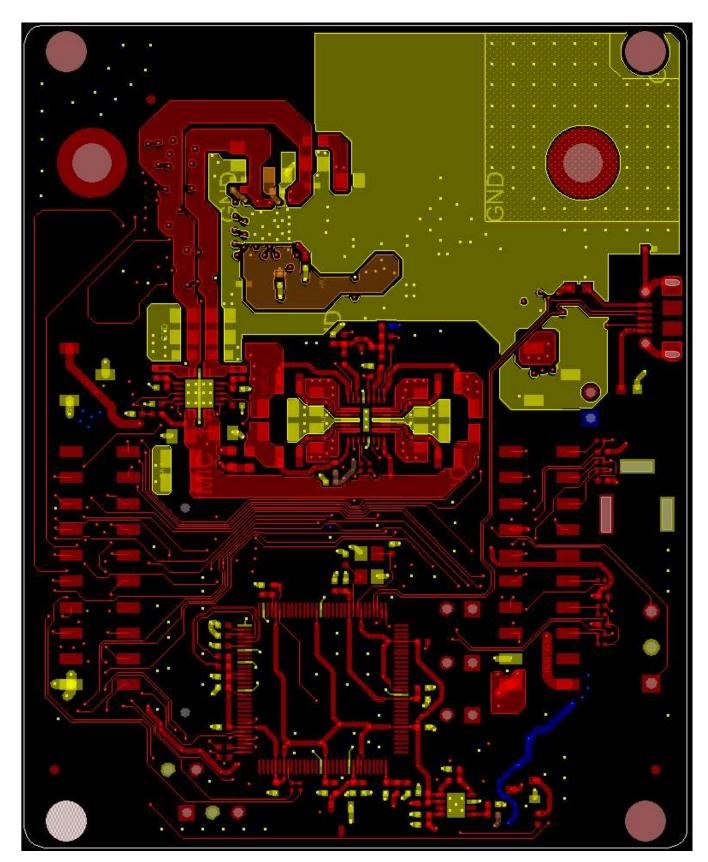
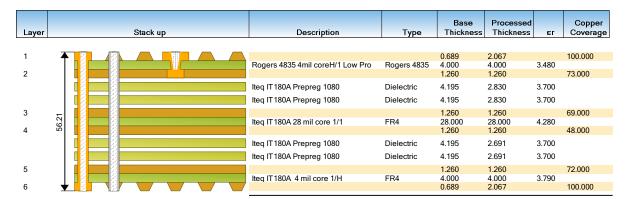


Figure 7-6. Bottom Layer Routing



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# 7.4.2 Stackup Details



## 8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions follow.

## 8.1 Device Nomenclature

To designate the stages in the product development cycle, TI assigns prefixes to the part numbers of all microprocessors (MPUs) and support tools. Each device has one of three prefixes: X, P, or null (no prefix) (for example, *AWR1243*). Texas Instruments recommends two of three possible prefix designators for its support tools: TMDX and TMDS. These prefixes represent evolutionary stages of product development from engineering prototypes (TMDX) through fully qualified production devices and tools (TMDS).

Device development evolutionary flow:

**X** Experimental device that is not necessarily representative of the final device's electrical specifications and may not use production assembly flow.

Prototype device that is not necessarily the final silicon die and may not necessarily meet final electrical specifications.

**null** Production version of the silicon die that is fully qualified.

Support tool development evolutionary flow:

TMDX Development-support product that has not yet completed Texas Instruments internal

qualification testing.

**TMDS** Fully-qualified development-support product.

X and P devices and TMDX development-support tools are shipped against the following disclaimer:

"Developmental product is intended for internal evaluation purposes."

Production devices and TMDS development-support tools have been characterized fully, and the quality and reliability of the device have been demonstrated fully. Tl's standard warranty applies.

Predictions show that prototype devices (X or P) have a greater failure rate than the standard production devices. Texas Instruments recommends that these devices not be used in any production system because their expected end-use failure rate still is undefined. Only qualified production devices are to be used.

TI device nomenclature also includes a suffix with the device family name. This suffix indicates the package type (for example, ABL0161), the temperature range (for example, blank is the default commercial temperature range). Figure 8-1 provides a legend for reading the complete device name for any *AWR1243* device.

For orderable part numbers of *AWR1243* devices in the ABL0161 package types, see the Package Option Addendum of this document, the TI website (www.ti.com), or contact your TI sales representative.

For additional description of the device nomenclature markings on the die, see the *AWR1243 Device Errata Silicon Revision 1.0 and 2.0.* 



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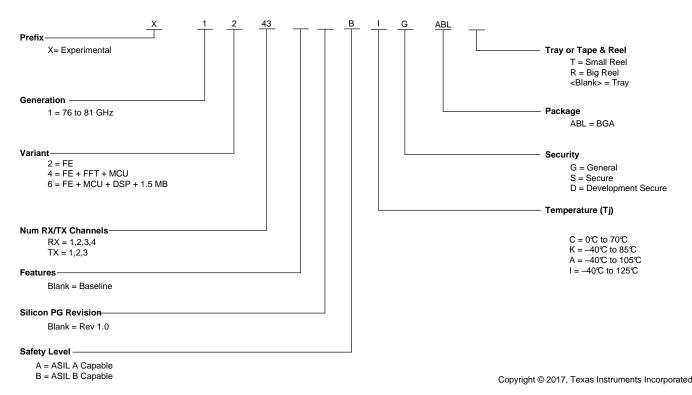


Figure 8-1. Device Nomenclature

#### 8.2 **Tools and Software**

## **Models**

AWR1243 BSDL Model Boundary scan database of testable input and output pins for IEEE 1149.1 of the specific device.

AWR1x43 IBIS Model IO buffer information model for the IO buffers of the device. For simulation on a circuit board, see IBIS Open Forum.

AWR1243 Checklist for Schematic Review, Layout Review, Bringup/Wakeup A set of steps in spreadsheet form to select system functions and pinmux options. Specific EVM schematic and layout notes to apply to customer engineering. A bringup checklist is suggested for customers.

### 8.3 **Documentation Support**

To receive notification of documentation updates—including silicon errata—go to the product folder for your device on ti.com (AWR1243). In the upper right-hand corner, click the "Alert me" button. This registers you to receive a weekly digest of product information that has changed (if any). For change details, check the revision history of any revised document.

The current documentation that describes the DSP, related peripherals, and other technical collateral follows.

## **Errata**

AWR1243 Device Errata Describes known advisories, limitations, and cautions on silicon and provides workarounds.



SWRS188-MAY 2017 www.ti.com

#### 8.4 **Community Resources**

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community The TI engineer-to-engineer (E2E) community was created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

TI Embedded Processors Wiki Established to help developers get started with Embedded Processors from Texas Instruments and to foster innovation and growth of general knowledge about the hardware and software surrounding these devices.

#### 8.5 **Trademarks**

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

### 8.6 **Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 8.7 **Export Control Notice**

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#### 8.8 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.



# 9 Mechanical, Packaging, and Orderable Information

# 9.1 Packaging Information

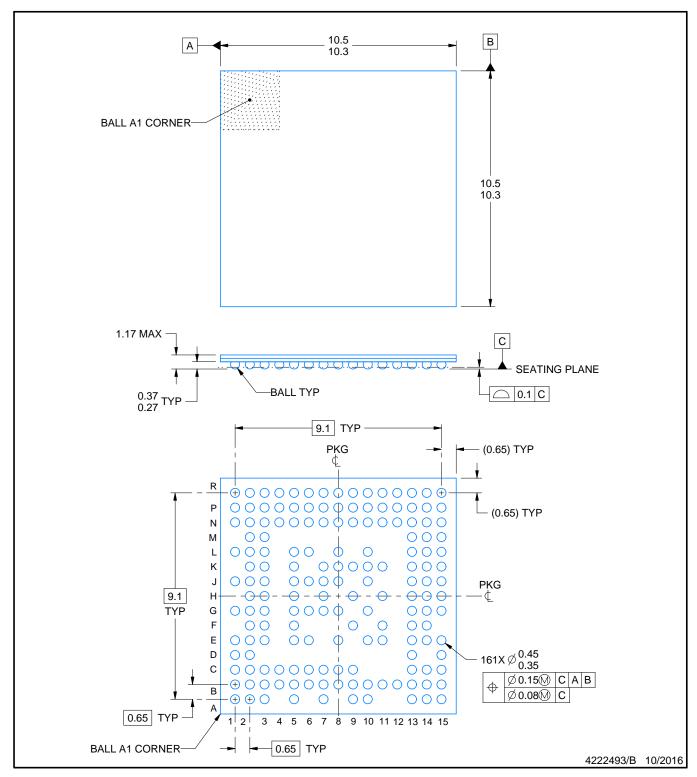
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

### **CAUTION**

The following package information is subject to change without notice.



PLASTIC BALL GRID ARRAY

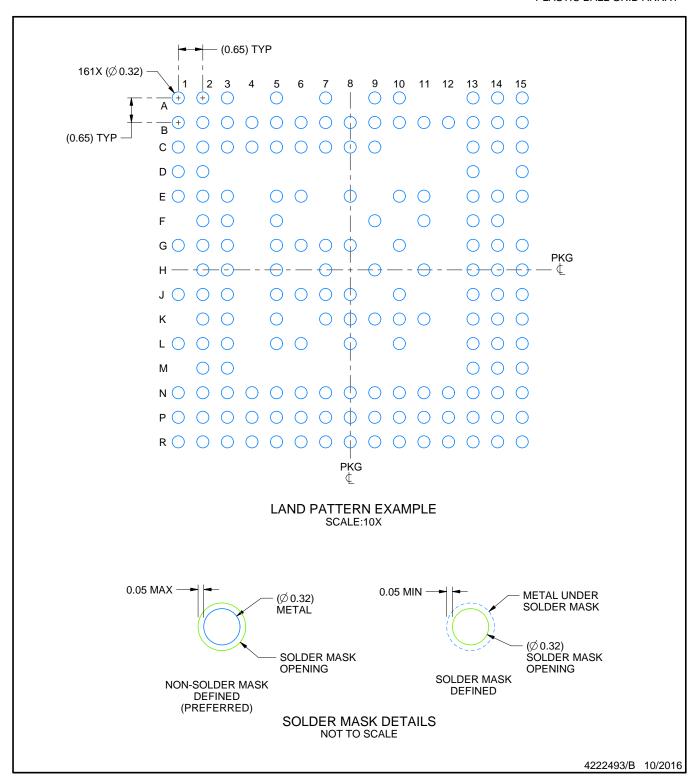


## NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



PLASTIC BALL GRID ARRAY

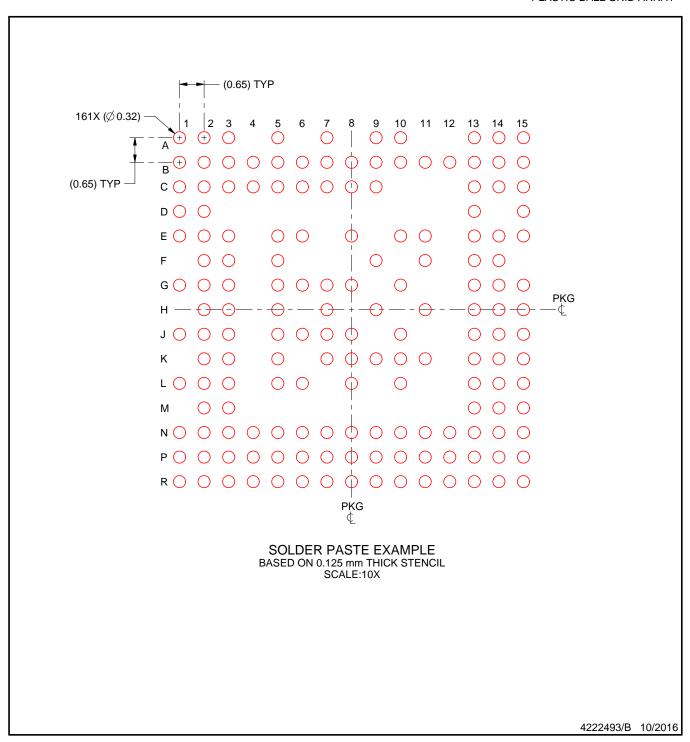


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For information, see Texas Instruments literature number SPRAA99 (www.ti.com/lit/spraa99).



PLASTIC BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.





# PACKAGE OPTION ADDENDUM

15-May-2017

## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
X1243BIGABL	ACTIVE	FC/CSP	ABL	161	1	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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